

Notice of References Cited

Application/Control No.

09/648,111

Applicant(s)/Patent Under
Reexamination
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Examiner

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Art Unit

2815

Page 1 of 1

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*		Document Number		Date MM-YYYY	Name	Classification	
		Country Code-Number-Kind Code					
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	B	US-5968847-a		10-1999	Ye et al.	437	228
	C	US-5771110-a		06-1998	Hirano et al.	257	72
	D	US-5723366-a		03-1998	Suzuki et al.	438	--
	E	US-5843277-a		12-1998	Goto et al.	156	643.1
	F	US- -					
	G	US- -					
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	I	US- -					
	J	US- -					
	K	US- -					
	L	US- -					
	M	US- -					

FOREIGN PATENT DOCUMENTS

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		Country Code-Number-Kind Code						
	N	jp-408043857-a		02-1996	Japan	Hirano et al.	--	--
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	M. Mhri et al., Plasma Etching of ITO Thin Films Using a CH ₄ /H ₂ Gas Mixture, Japanese Journal of Applied Physics, vol. 29, No. 10, Oct., 1990, pp. L 1932-L 1935.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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